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Advanced Etch Technology for Nanopatterning III

Gottlieb S. Oehrlein
Qinghuang Lin
Editors

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Introduction

This proceedings volume contains selected papers presented at the conference Advanced Etch Technology for Nanopatterning III held February 24-25, 2014 as part of the SPIE Advanced Lithography Symposium 2014. The meeting featured six sessions of oral presentations to highlight important achievements and challenges in the following areas of Advanced Etch Technology for Nanopatterning:

Session 1: Reviews and Overviews of Nanopatterning Challenges

Session 2: Nanopatterning for Advanced Logic and Memory Technology Nodes

Session 3: Plasma and Resist Interactions, Including Patterning Quality Control (LER, CD Uniformity, etc.)

Session 4: Patterning Integration Schemes (multilayer patterning, self-aligned patterning, etc.)

Session 5: New Plasma Sources and New Etching Technologies

Session 6: Emerging Patterning Technologies (DSA and others)

Additionally, there was a poster session.

We would like to thank all speakers and presenters for their stimulating contributions to the conference. We also would like to express our gratitude to the SPIE Advanced Lithography "Advanced Etch Technology for Nanopatterning III" Conference Committee members for their contributions in organizing this very successful conference. Finally, we would like to thank SPIE and its staff for support of this conference and their arrangements.

Gottlieb S. Oehrlein
Qinghuang Lin